# ne<mark>x</mark>peria

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In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

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Should be replaced with:

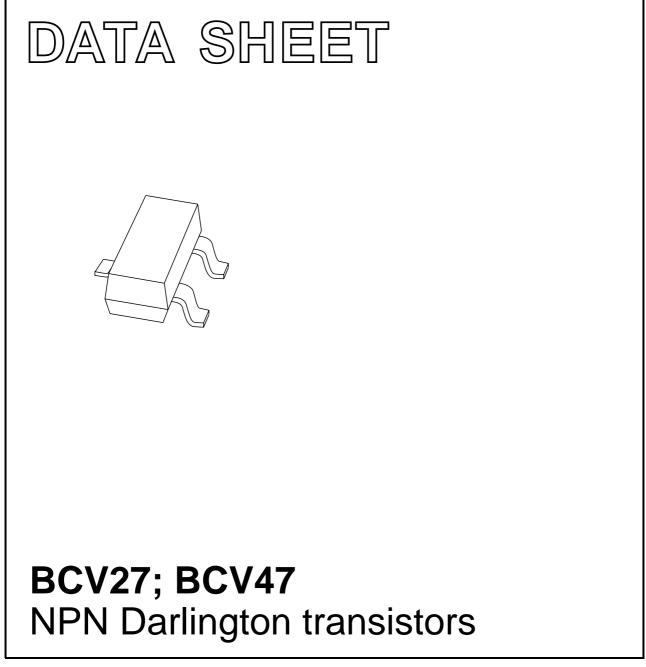
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

## DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1999 Apr 08 2004 Jan 13



#### FEATURES

- Medium current (max. 500 mA)
- Low voltage (max. 60 V)
- High DC current gain (min. 20000).

#### APPLICATIONS

• Preamplifier input applications.

#### DESCRIPTION

NPN Darlington transistor in a SOT23 plastic package. PNP complements: BCV26 and BCV46.

#### MARKING

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
BCV27	FF*
BCV47	FG*

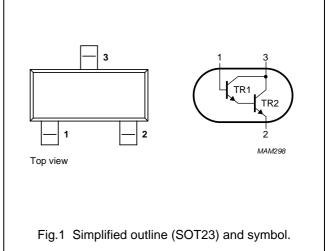
#### Note

- 1. \* = p : Made in Hong Kong.
  - \* = t : Made in Malaysia.
  - \* = W : Made in China.

#### **ORDERING INFORMATION**

#### PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



TYPE	PACKAGE		
NUMBER	NAME DESCRIPTION		VERSION
BCV27	_	plastic surface mounted package; 3 leads	SOT23
BCV47			

## **BCV27; BCV47**

## BCV27; BCV47

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BCV27		-	40	V
	BCV47		-	80	V
V <sub>CES</sub>	collector-emitter voltage	open base			
	BCV27		-	30	V
	BCV47		-	60	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	10	V
I <sub>C</sub>	collector current (DC)		-	500	mA
I <sub>CM</sub>	peak collector current		-	800	mA
I <sub>B</sub>	base current		-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$ ; note 1	-	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	500	K/W

#### Note

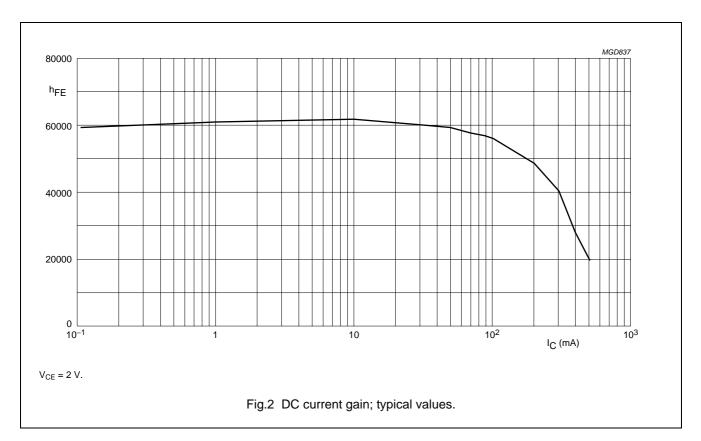
1. Transistor mounted on an FR4 printed-circuit board.

# BCV27; BCV47

#### CHARACTERISTICS

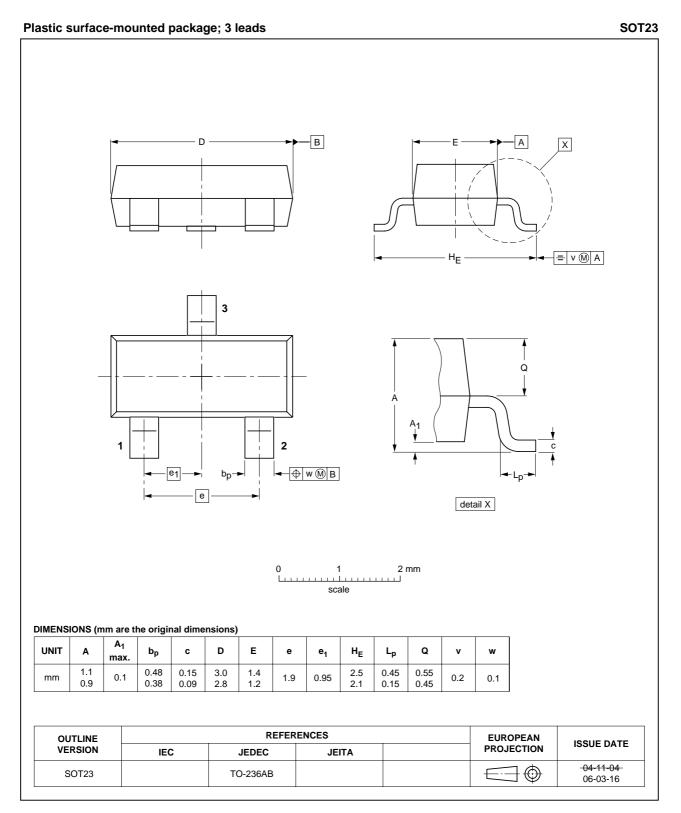
 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current					
	BCV27	I <sub>E</sub> = 0; V <sub>CBO</sub> = 30 V	-	_	100	nA
	BCV47	I <sub>E</sub> = 0; V <sub>CBO</sub> = 60 V	-	_	100	nA
I <sub>EBO</sub>	emitter cut-off current	I <sub>E</sub> = 0; V <sub>EB</sub> = 10 V	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; (see Fig.2)				
	BCV27	$I_{\rm C} = 1  \rm{mA}$	4 000	_	_	
		I <sub>C</sub> = 10 mA	10000	_	_	
		I <sub>C</sub> = 100 mA	20000	_	_	
	DC current gain	V <sub>CE</sub> = 5 V; (see Fig.2)				
	BCV47	$I_{\rm C} = 1  \rm{mA}$	2000	_	_	
		I <sub>C</sub> = 10 mA	4 000	_	-	
		I <sub>C</sub> = 100 mA	10000	_	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 100 mA; I <sub>B</sub> = 0.1 mA	-	_	1	V
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 100 mA; I <sub>B</sub> = 0.1 mA	_	-	1.5	V
V <sub>BEon</sub>	base-emitter on-state voltage	I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 5 V	-	-	1.4	V
f <sub>T</sub>	transition frequency	$I_{C} = 30 \text{ mA}; V_{CE} = 5 \text{ V}; \text{ f} = 100 \text{ MHz}$	_	220	_	MHz



# BCV27; BCV47

#### PACKAGE OUTLINE



### BCV27; BCV47

#### DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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## **NXP Semiconductors**

#### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

#### **Contact information**

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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